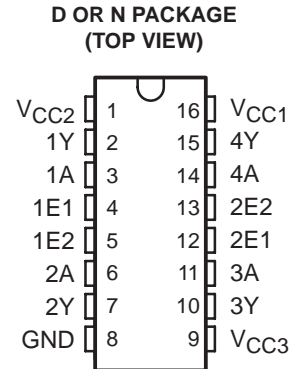# SN75374
QUADRUPLE MOSFET DRIVER

SLRS028A – SEPTEMBER 1988 – REVISED NOVEMBER 2004

- **Quadruple Circuits Capable of Driving High-Capacitance Loads at High Speeds**
- **Output Supply Voltage Range From 5 V to 24 V**
- **Low Standby Power Dissipation**
- **V_{CC3} Supply Maximizes Output Source Voltage**

D OR N PACKAGE
(TOP VIEW)

V_{CC2}	1		16	V_{CC1}
1Y	2		15	4Y
1A	3		14	4A
1E1	4		13	2E2
1E2	5		12	2E1
2A	6		11	3A
2Y	7		10	3Y
GND	8		9	V_{CC3}

description/ordering information

The SN75374 is a quadruple NAND interface circuit designed to drive power MOSFETs from TTL inputs. It provides the high current and voltage necessary to drive large capacitive loads at high speeds.

The outputs can be switched very close to the V_{CC2} supply rail when V_{CC3} is about 3 V higher than V_{CC2}. V_{CC3} also can be tied directly to V_{CC2} when the source voltage requirements are lower.
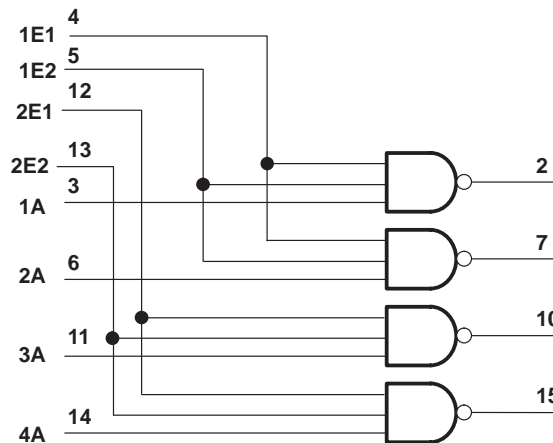
ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	PDIP (N)	Tube of 25	SN75374N	SN75374N
	SOIC (D)	Tube of 40	SN75374D	SN75374
		Reel of 2500	SN75374DR	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

logic diagram (positive logic)

TEXAS INSTRUMENTS

SN75374
QUADRUPLE MOSFET DRIVER

schematic (each driver)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range (see Note 1): V_{CC1}	−0.5 V to 7 V
V_{CC2}	−0.5 V to 25 V
V_{CC3}	−0.5 V to 30 V
Input voltage, V_I	5.5 V
Peak output current, I_I (t_w < 10 ms, duty cycle < 50%)	500 mA
Package thermal impedance, θ_{JA} (see Notes 2 and 3): D package	73°C/W
N package	67°C/W
Operating virtual junction temperature, T_J	150°C
Storage temperature range, T_{stg}	−65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Voltage values are with respect to network ground terminal.
2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

		MIN	NOM	MAX	UNIT
V_{CC1}	Supply voltage	4.75	5	5.25	V
V_{CC2}	Supply voltage	4.75	20	24	V
V_{CC3}	Supply voltage	V_{CC2}	24	28	V
$V_{CC3} - V_{CC2}$	Voltage difference between supply voltages	0	4	10	V
V_{IH}	High-level input voltage	2			V
V_{IL}	Low-level input voltage			0.8	V
I_{OH}	High-level output current			−10	mA
I_{OL}	Low-level output current			40	mA
T_A	Operating free-air temperature	0		70	°C

TEXAS
INSTRUMENTS

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electrical characteristics over recommended ranges of V_{CC1}, V_{CC2}, V_{CC3}, and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}	Input clamp voltage	$I_I = -12$ mA					-1.5	V
V_{OH}	High-level output voltage	$V_{CC3} = V_{CC2} + 3$ V,	$V_{IL} = 0.8$ V,	$I_{OH} = -100$ μA	$V_{CC2} - 0.3$	$V_{CC2} - 0.1$		V
		$V_{CC3} = V_{CC2} + 3$ V,	$V_{IL} = 0.8$ V,	$I_{OH} = -10$ mA	$V_{CC2} - 1.3$	$V_{CC2} - 0.9$		
		$V_{CC3} = V_{CC2}$,	$V_{IL} = 0.8$ V,	$I_{OH} = -50$ μA	$V_{CC2} - 1$	$V_{CC2} - 0.7$		
		$V_{CC3} = V_{CC2}$,	$V_{IL} = 0.8$ V,	$I_{OH} = -10$ mA	$V_{CC2} - 2.5$	$V_{CC2} - 1.8$		
V_{OL}	Low-level output voltage	$V_{IH} = 2$ V,	$I_{OL} = 10$ mA			0.15	0.3	V
		$V_{CC2} = 15$ V to 28 V,	$V_{IH} = 2$ V,	$I_{OL} = 40$ mA		0.25	0.5	
V_F	Output clamp-diode forward voltage	$V_I = 0$,	$I_F = 20$ mA				1.5	V
I_I	Input current at maximum input voltage	$V_I = 5.5$ V					1	mA
I_{IH}	High-level input current	Any A	$V_I = 2.4$ V				40	μA
		Any E					80	
I_{IL}	Low-level input current	Any A	$V_I = 0.4$ V			-1	-1.6	mA
		Any E				-2	-3.2	
$I_{CC1(H)}$	Supply current from V_{CC1}, all outputs high	$V_{CC1} = 5.25$ V, $V_{CC2} = 24$ V, $V_{CC3} = 28$ V, All inputs at 0 V, No load				4	8	mA
$I_{CC2(H)}$	Supply current from V_{CC2}, all outputs high					-2.2	0.25	
$I_{CC3(H)}$	Supply current from V_{CC3}, all outputs high					2.2	3.5	
$I_{CC1(L)}$	Supply current from V_{CC1}, all outputs low	$V_{CC1} = 5.25$ V, $V_{CC2} = 24$ V, $V_{CC3} = 28$ V, All inputs at 5 V, No load				31	47	mA
$I_{CC2(L)}$	Supply current from V_{CC2}, all outputs low						2	
$I_{CC3(L)}$	Supply current from V_{CC1}, all outputs low					16	27	
$I_{CC2(H)}$	Supply current from V_{CC2}, all outputs high	$V_{CC1} = 5.25$ V, $V_{CC2} = 24$ V, $V_{CC3} = 24$ V, All inputs at 0 V, No load					0.25	mA
$I_{CC3(H)}$	Supply current from V_{CC3}, all outputs high						0.5	
$I_{CC2(S)}$	Supply current from V_{CC2}, standby condition	$V_{CC1} = 0$, $V_{CC2} = 24$ V, $V_{CC3} = 24$ V, All inputs at 0 V, No load					0.25	mA
$I_{CC3(S)}$	Supply current from V_{CC3}, standby condition						0.5	

† All typical values are at $V_{CC1} = 5$ V, $V_{CC2} = 20$ V, $V_{CC3} = 24$ V, and $T_A = 25°C$, except for V_{OH} for which V_{CC2} and V_{CC3} are as stated under test conditions.

switching characteristics, $V_{CC1} = 5$ V, $V_{CC2} = 20$ V, $V_{CC3} = 24$ V, $T_A = 25°C$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{DLH}	Delay time, low- to high-level output	$C_L = 200$ pF, $R_D = 24$ Ω, See Figure 1		20	30	ns
t_{DHL}	Delay time, high- to low-level output			10	20	ns
t_{PLH}	Propagation delay time, low- to high-level output		10	40	60	ns
t_{PHL}	Propagation delay time, high- to low-level output		10	30	50	ns
t_{TLH}	Transition time, low- to high-level output			20	30	ns
t_{THL}	Transition time, high- to low-level output			20	30	ns

PARAMETER MEASUREMENT INFORMATION

TEST CIRCUIT
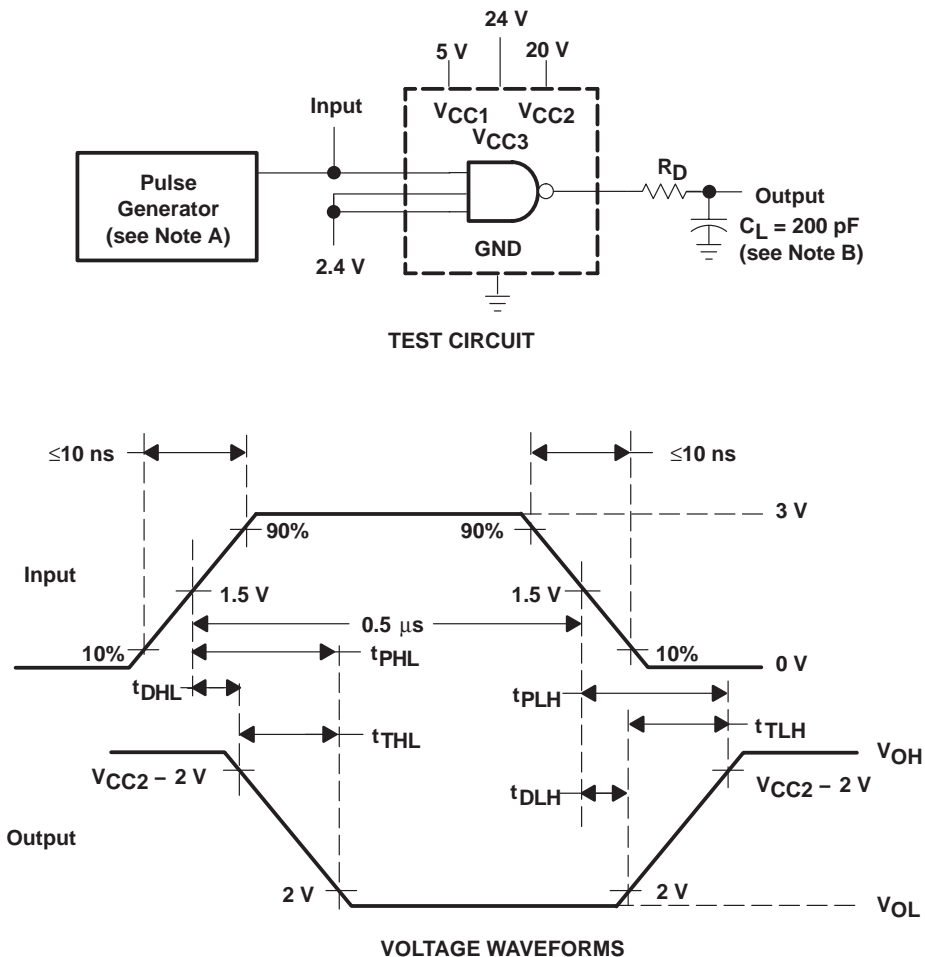
VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR = 1 MHz, $Z_O \approx 50\ \Omega$.
      B. C_L includes probe and jig capacitance.

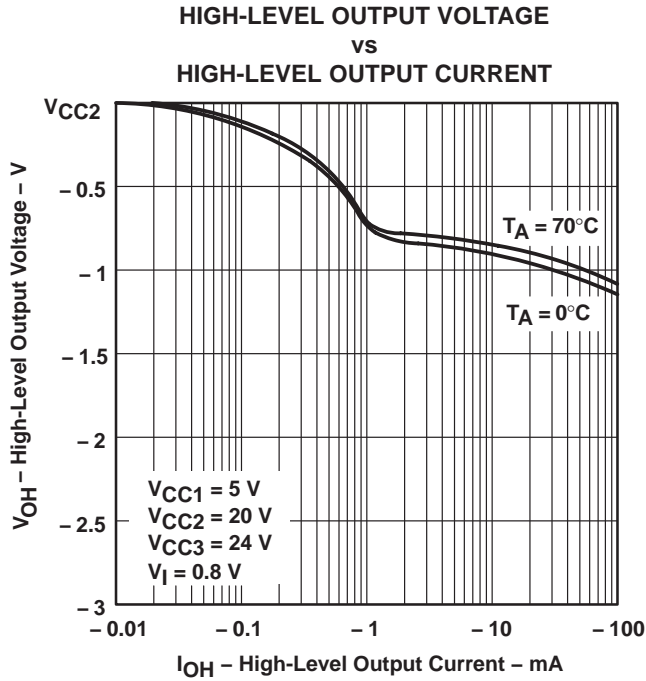**Figure 1. Test Circuit and Voltage Waveforms, Each Driver**
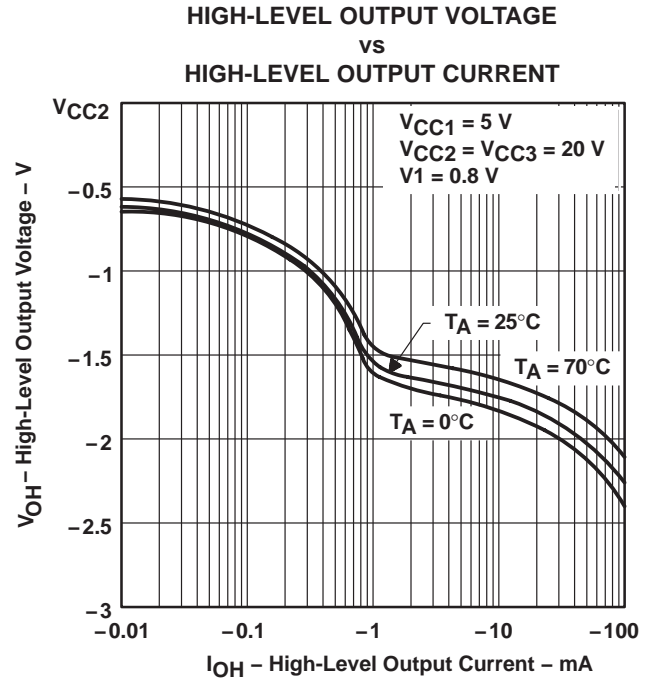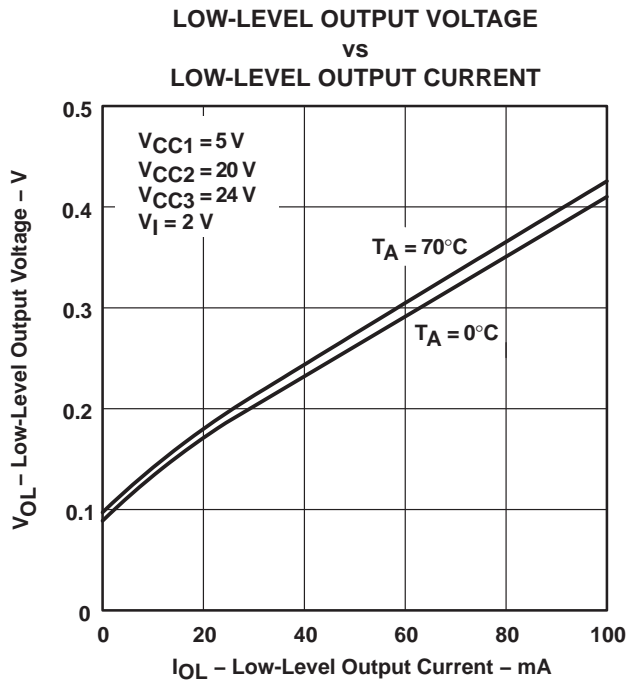
TYPICAL CHARACTERISTICS

HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

$V_{CC1} = 5$ V
$V_{CC2} = 20$ V
$V_{CC3} = 24$ V
$V_I = 0.8$ V

$T_A = 70°C$
$T_A = 0°C$

V_{OH} – High-Level Output Voltage – V
I_{OH} – High-Level Output Current – mA

Figure 2

HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

$V_{CC1} = 5$ V
$V_{CC2} = V_{CC3} = 20$ V
$V1 = 0.8$ V

$T_A = 25°C$
$T_A = 70°C$
$T_A = 0°C$

V_{OH} – High-Level Output Voltage – V
I_{OH} – High-Level Output Current – mA

Figure 3

LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

$V_{CC1} = 5$ V
$V_{CC2} = 20$ V
$V_{CC3} = 24$ V
$V_I = 2$ V

$T_A = 70°C$
$T_A = 0°C$

V_{OL} – Low-Level Output Voltage – V
I_{OL} – Low-Level Output Current – mA

Figure 4

VOLTAGE TRANSFER CHARACTERISTICS

$V_{CC1} = 5$ V
$V_{CC2} = 20$ V
$V_{CC3} = 24$ V
$T_A = 25°C$
No Load

V_O – Output Voltage – V
V_I – Input Voltage – V

Figure 5

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TYPICAL CHARACTERISTICS

**PROPAGATION DELAY TIME
LOW- TO HIGH-LEVEL OUTPUT
vs
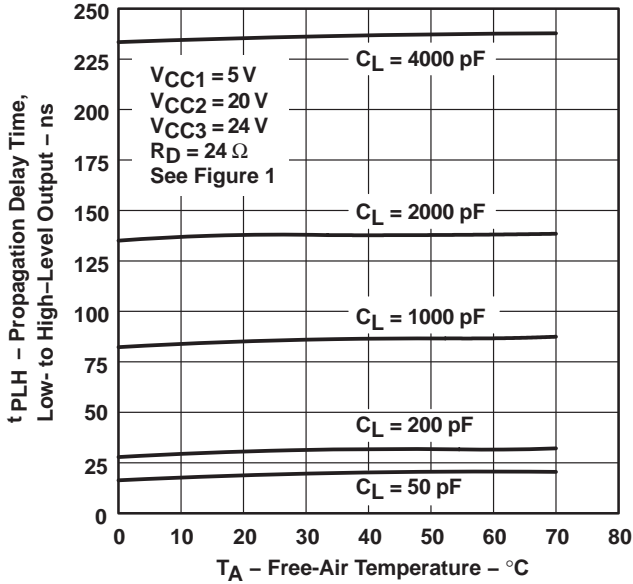FREE-AIR TEMPERATURE**

Figure 6

**PROPAGATION DELAY TIME
HIGH- TO LOW-LEVEL OUTPUT
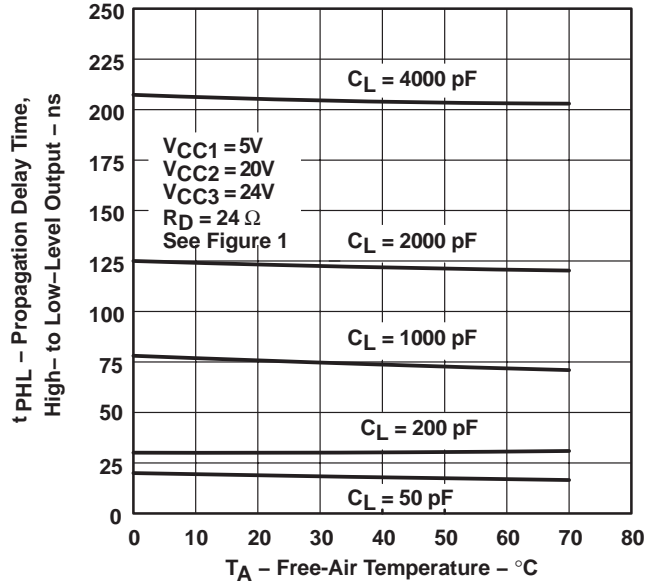vs
FREE-AIR TEMPERATURE**

Figure 7

**PROPAGATION DELAY TIME
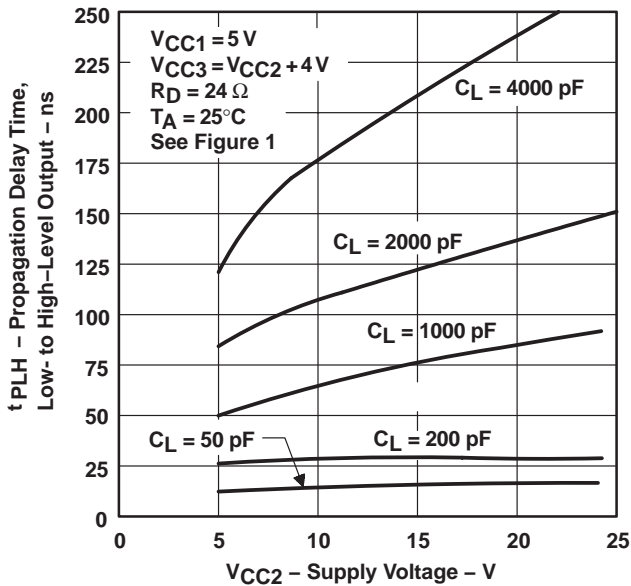LOW-TO HIGH-LEVEL OUTPUT
vs
V_{CC2} SUPPLY VOLTAGE**

Figure 8

**PROPAGATION DELAY TIME
HIGH- TO LOW-LEVEL OUTPUT
vs
V_{CC2} SUPPLY VOLTAGE**
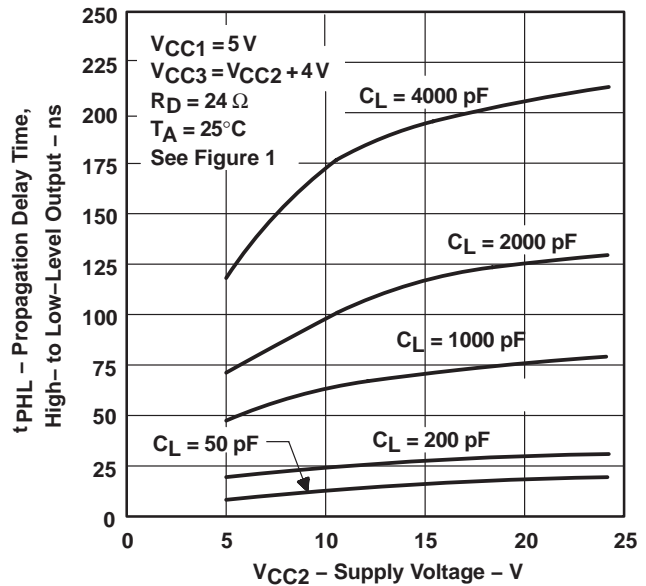
Figure 9

TYPICAL CHARACTERISTICS

**PROPAGATION DELAY TIME
LOW- TO HIGH-LEVEL OUTPUT
vs
LOAD CAPACITANCE**

Figure 10

**PROPAGATION DELAY TIME
HIGH- TO LOW-LEVEL OUTPUT
vs
LOAD CAPACITANCE**
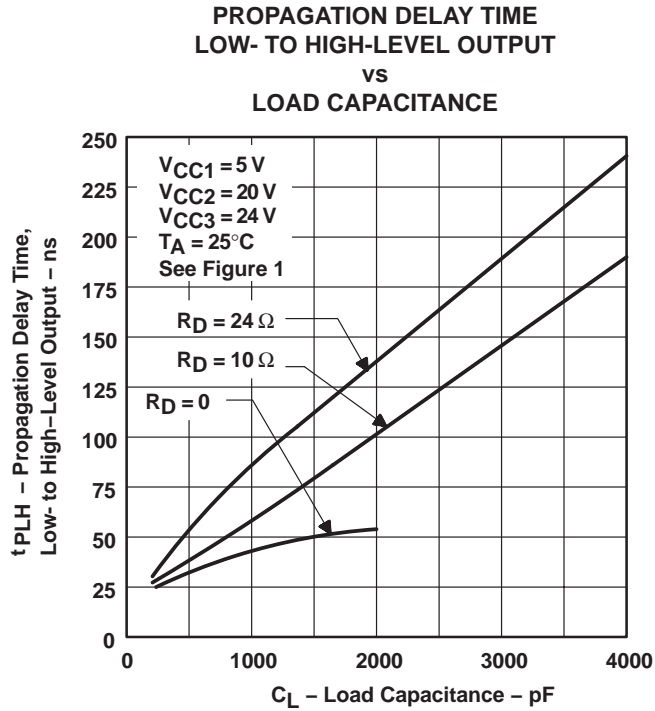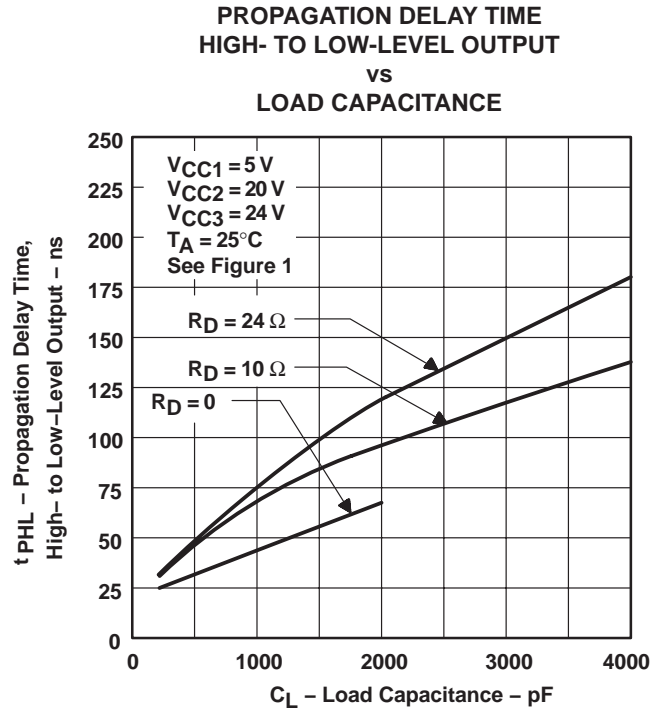

Figure 11

**POWER DISSIPATION (ALL DRIVERS)
vs
FREQUENCY**
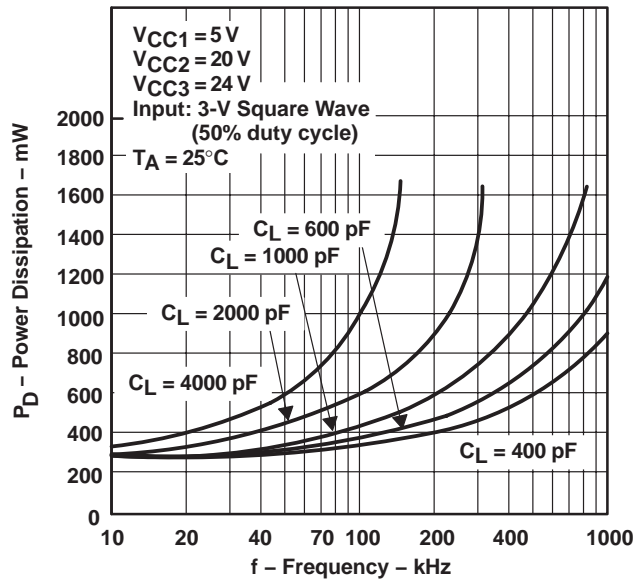
Figure 12

NOTE: For $R_D = 0$, operation with $C_L > 2000$ pF violates absolute maximum current rating.

THERMAL INFORMATION

power-dissipation precautions

Significant power may be dissipated in the SN75374 driver when charging and discharging high-capacitance loads over a wide voltage range at high frequencies. Figure 12 shows the power dissipated in a typical SN75374 as a function of frequency and load capacitance. Average power dissipated by this driver is derived from the equation:

$$P_{T(AV)} = P_{DC(AV)} + P_{C(AV)} + P_{S(AV)}$$

where $P_{DC(AV)}$ is the steady-state power dissipation with the output high or low, $P_{C(AV)}$ is the power level during charging or discharging of the load capacitance, and $P_{S(AV)}$ is the power dissipation during switching between the low and high levels. None of these include energy transferred to the load, and all are averaged over a full cycle.

The power components per driver channel are:

$$P_{DC(AV)} = \frac{(P_H t_H + P_L t_L)}{T}$$

$$P_{C(AV)} \approx CV^2_C f$$

$$P_{S(AV)} = \frac{(P_{LH} t_{LH} + P_{HL} t_{HL})}{T}$$
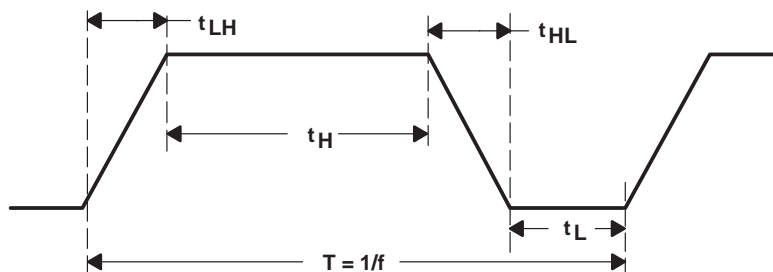
where the times are as defined in Figure 15.

Figure 13. Output-Voltage Waveform

THERMAL INFORMATION

power-dissipation precautions (continued)

P_L, P_H, P_{LH}, and P_{HL} are the respective instantaneous levels of power dissipation, and C is the load capacitance. V_C is the voltage across the load capacitance during the charge cycle shown by the equation:

$$V_C = V_{OH} - V_{OL}$$

$P_{S(AV)}$ may be ignored for power calculations at low frequencies.

In the following power calculation, all four channels are operating under identical conditions: f = 0.2 MHz, V_{OH} = 19.9 V and V_{OL} = 0.15 V with V_{CC1} = 5 V, V_{CC2} = 20 V, V_{CC3} = 24 V, V_C = 19.75 V, C = 1000 pF, and the duty cycle = 60%. At 0.2 MHz for C_L < 2000 pF, $P_{S(AV)}$ is negligible and can be ignored. When the output voltage is low, I_{CC2} is negligible and can be ignored.

On a per-channel basis using data-sheet values,

$$P_{DC(AV)} = \left[5\,V\left(\frac{4\,mA}{4}\right) + 20\,V\left(\frac{-2.2\,mA}{4}\right) + 24\,V\left(\frac{2.2\,mA}{4}\right) \right] 0.6 +$$

$$\left[5\,V\left(\frac{31\,mA}{4}\right) + 20\,V\left(\frac{0\,mA}{4}\right) + 24\,V\left(\frac{16\,mA}{4}\right) \right] 0.4$$

$P_{DC(AV)}$ = 58.2 mW per channel

Power during the charging time of the load capacitance is

$$P_{C(AV)} = (1000\,pF)(19.75\,V)^2(0.2\,MHz) = 78\,mW \text{ per channel}$$

Total power for each driver is:

$$P_{T(AV)} = 58.2\,mW + 78\,mW = 136.2\,mW$$

The total package power is:

$$P_{T(AV)} = (136.2)(4) = 544.8\,mW$$

SN75374
QUADRUPLE MOSFET DRIVER

APPLICATION INFORMATION

driving power MOSFETs

The drive requirements of power MOSFETs are much lower than comparable bipolar power transistors. The input impedance of an FET consists of a reverse-biased PN junction that can be described as a large capacitance in parallel with a very high resistance. For this reason, the commonly used open-collector driver with a pullup resistor is not satisfactory for high-speed applications. In Figure 14a, an IRF151 power MOSFET switching an inductive load is driven by an open-collector transistor driver with a 470-Ω pullup resistor. The input capacitance (C_{ISS}) specification for an IRF151 is 4000 pF maximum. The resulting long turn-on time, due to the product of input capacitance and the pullup resistor, is shown in Figure 14b.
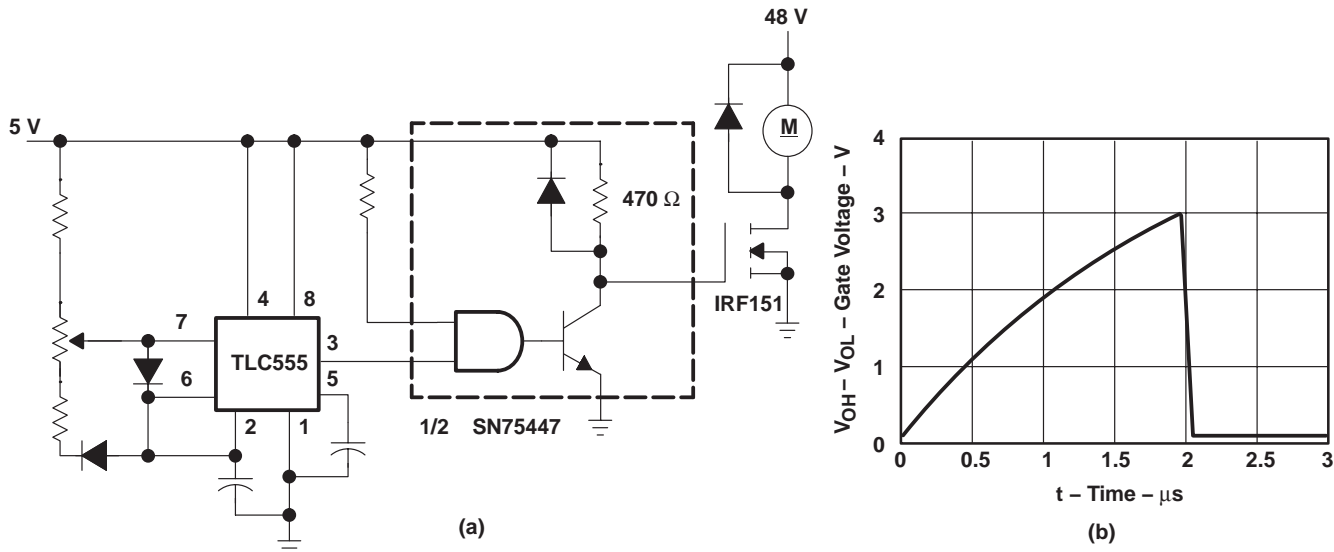
Figure 14. Power MOSFET Drive Using SN75447

A faster, more efficient drive circuit uses an active pullup, as well as an active pulldown output configuration, referred to as a totem-pole output. The SN75374 driver provides the high-speed totem-pole drive desired in an application of this type (see Figure 15a). The resulting faster switching speeds are shown in Figure 15b.
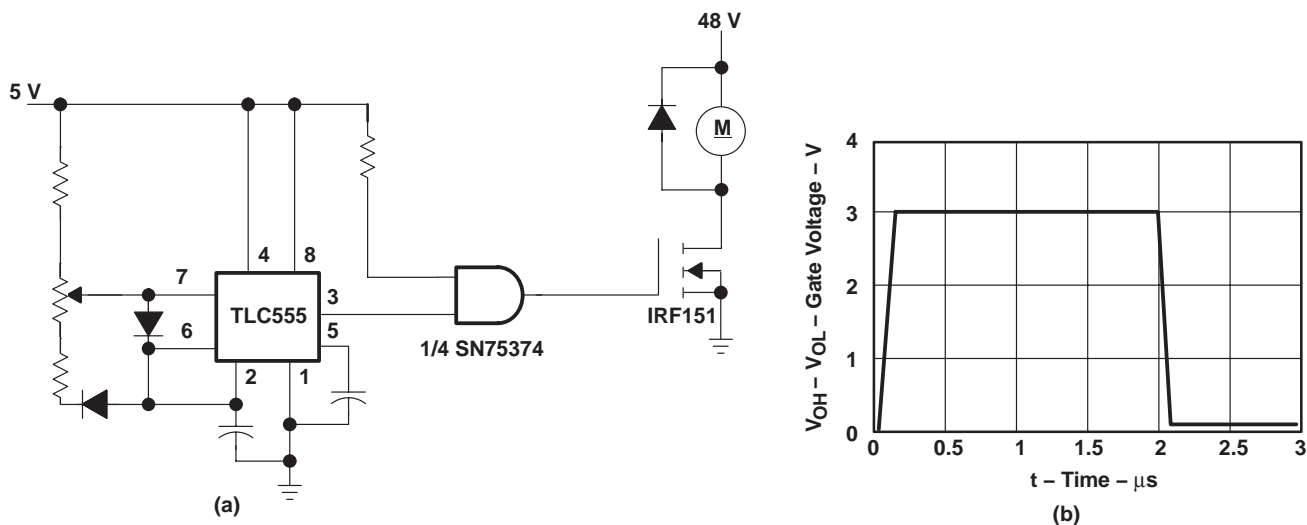
Figure 15. Power MOSFET Drive Using SN75374

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APPLICATION INFORMATION

driving power MOSFETs (continued)

Power MOSFET drivers must be capable of supplying high peak currents to achieve fast switching speeds as shown by the equation:

$$I_{PK} = \frac{VC}{t_r}$$

where C is the capacitive load and t_r is the desired rise time. V is the voltage that the capacitance is charged to. In the circuit shown in Figure 14a, V is found by the equation:

$$V = V_{OH} - V_{OL}$$

Peak current required to maintain a rise time of 100 ns in the circuit of Figure 14a is:

$$I_{PK} = \frac{(3 - 0)4(10^{-9})}{100(10^{-9})} = 120 \text{ mA}$$

Circuit capacitance can be ignored because it is very small compared to the input capacitance of the IRF151. With a V_{CC} of 5 V and assuming worst-case conditions, the gate drive voltage is 3 V.

For applications in which the full voltage of V_{CC2} must be supplied to the MOSFET gate, V_{CC3} should be at least 3 V higher than V_{CC2}.

TEXAS
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PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
SN75374D	ACTIVE	SOIC	D	16	40	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN75374DR	ACTIVE	SOIC	D	16	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN75374N	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
None: Not yet available Lead (Pb-Free).
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

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N (R−PDIP−T)**

16 PINS SHOWN

PLASTIC DUAL−IN−LINE PACKAGE

DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS−001 VARIATION	AA	BB	AC	AD

0.260 (6,60)
0.240 (6,10)

0.070 (1,78)
0.045 (1,14)

0.045 (1,14)
0.030 (0,76)

0.020 (0,51) MIN

0.200 (5,08) MAX

Seating Plane

0.125 (3,18) MIN

0.100 (2,54)

0.021 (0,53)
0.015 (0,38)

⊕ 0.010 (0,25) Ⓜ

14/18 Pin Only
20 Pin vendor option

0.325 (8,26)
0.300 (7,62)

0.015 (0,38)

Gauge Plane

0.010 (0,25) NOM

0.430 (10,92) MAX

4040049/E 12/2002

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS−001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

D (R−PDSO−G16)   PLASTIC SMALL−OUTLINE PACKAGE

0.394 (10,00)
0.386 (9,80)

16   9

0.244 (6,20)
0.228 (5,80)

0.157 (4,00)
0.150 (3,80)

1   8

Pin 1
Index Area

0.050 (1,27)

0.020 (0,51)
0.012 (0,31)

⊕ 0.010 (0,25) Ⓜ

0.069 (1,75) Max

0.010 (0,25)
0.004 (0,10)

0.010 (0,25)
0.007 (0,17)

0.004 (0,10)

Gauge Plane

Seating Plane

0.010 (0,25)   0°−8°

0.050 (1,27)
0.016 (0,40)

4040047−4/F   07/2004

NOTES: A.   All linear dimensions are in inches (millimeters).
         B.   This drawing is subject to change without notice.
         C.   Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
         D.   Falls within JEDEC MS−012 variation AC.

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Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

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